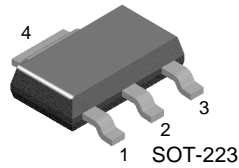


PZTA29

NPN Darlington Transistor

- This device designed for applications requiring extremely high current gain at collector currents to 500mA.
- Sourced from process 03.



1. Base 2.4. Collector 3. Emitter

Absolute Maximum Ratings * $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	100	V
V_{CBO}	Collector-Base Voltage	100	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current - Continuous	800	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady limits. The factory should be consulted on application involving pulsed or low duty cycle operations

Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units
Off Characteristics					
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100\mu\text{A}, V_{BE} = 0$	100		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\mu\text{A}, I_E = 0$	100		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	12		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 80\text{V}, I_E = 0$		100	nA
I_{CES}	Collector Cutoff Current	$V_{CE} = 80\text{V}, V_{BE} = 0$		500	nA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 10\text{V}, I_C = 0$		100	nA
On Characteristics					
h_{FE}	DC Current Gain	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$ $V_{CE} = 5.0\text{V}, I_C = 100\text{mA}$	10,000 10,000		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{mA}, I_B = 0.01\text{mA}$ $I_C = 100\text{mA}, I_B = 0.1\text{mA}$		1.2 1.5	V V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$		2.0	V
Small Signal characteristics					
f_T	Current Gain Bandwidth Product	$I_C = 10\text{mA}, V_{CE} = 5.0\text{V}, f = 100\text{MHz}$	125		MHz
C_{obo}	Output Capacitance	$V_{CB} = 1.0\text{V}, I_E = 0, f = 1.0\text{MHz}$		8.0	pF

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

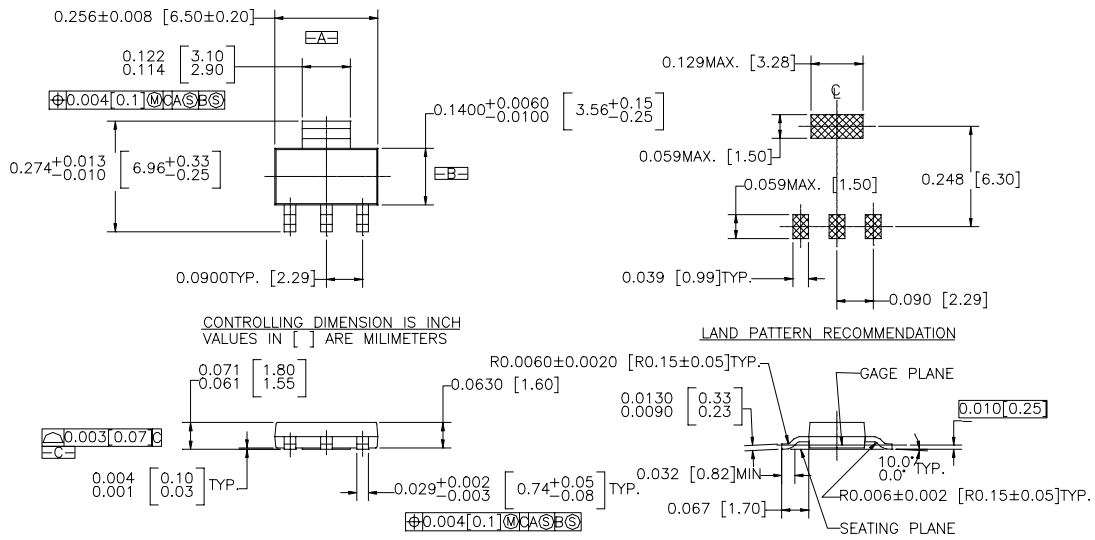
Thermal Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.	Units
P_D	Total Device Dissipation	1,000	mW
	Derate above 25°C	8.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	$^\circ\text{C}/\text{W}$

* Device mounted on FR-4PCB $36\text{mm} \times 18\text{mm} \times 1.5\text{mm}$; mounting pad for the collector lead min. 6cm^2

Mechanical Dimensions

SOT-223



CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS

LAND PATTERN RECOMMENDATION

- NOTES : UNLESS OTHERWISE SPECIFIED
 1. STANDARD LEAD FINISH TO BE 150 MICRONS/ 3.81 MICROMETERS
 MINIMUM TIN/LEAD (SOLDER) ON COPPER.
 2. REFERENCE JEDEC REGISTRATION TO-261, VARIATION AA, ISSUE A, DATED JAN 1990

SOT223, 4 LEADS

Dimensions in Millimeters

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE ^x ™	FAST [®]	IntelliMAX™	POP™	SPM™
ActiveArray™	FAST ^r ™	ISOPANAR™	Power247™	Stealth™
Bottomless™	FPS™	LittleFET™	PowerEdge™	SuperFET™
CoolFET™	FRFET™	MICROCOUPLER™	PowerSaver™	SuperSOT™-3
CROSSVOLT™	GlobalOptoisolator™	MicroFET™	PowerTrench [®]	SuperSOT™-6
DOME™	GTO™	MicroPak™	QFET [®]	SuperSOT™-8
EcoSPARK™	HiSeC™	MICROWIRE™	QS™	SyncFET™
E ² CMOST™	I ² C™	MSX™	QT Optoelectronics™	TinyLogic [®]
EnSigna™	<i>i-Lo</i> ™	MSXPro™	Quiet Series™	TINYOPTO™
FACT™	ImpliedDisconnect™	OCX™	RapidConfigure™	TruTranslation™
FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
Across the board. Around the world.™		OPTOLOGIC [®]	μ SerDes™	UltraFET [®]
The Power Franchise [®]		OPTOPLANAR™	SILENT SWITCHER [®]	UniFET™
Programmable Active Droop™		PACMAN™	SMART START™	VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I15